

微小電界センサによる無バイアスでのIGBT 欠陥観察

Non-bias IGBT defect observation using a nano-electro field probe sensor

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Abstract

The nano-electro field probe sensor (NEPS) method is a technique to estimate a failure region by imaging the change of the carrier signal that is generated by irradiating the laser under non-electrical contact and non-bias condition. We report the result that NEPS detects the contact and the trench defect on TEG of IGBT.